Supplementary Information

Filling the gap between topological insulator nanomaterials and

triboelectric nanogenerators

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Supplementary Figure 1 | Fabrication process of the TI-TENG using Bi2Te³ NPs. Schematic illustration of the fabrication of TI-TENG, which was composed of indium tin oxide (ITO), polyethylene terephthalate (PET), and $Bi₂Te₃$ -NP film, serving as the electrode, substrate, and TI triboelectric layer, respectively. For fabricating the top TI-based triboelectric part (a), the as-synthesized Bi₂Te₃ NPs were firstly dispersed into isopropanol with a suitable concentration to form a homogeneous Bi_2Te_3-NP colloid. A certain dosage of Bi_2Te_3-NP colloid was then uniformly coated on the surface of the PET substrate, which is single-side conductive with ITO film on the bottom. Note that Kapton tape was attached to the substrate all around to mold the Bi_2Te_3-NP film. For fabricating the bottom counterpart (b, taking Kapton as an example), a Kapton film was attached on the top of the PET substrate and ITO also acts as the bottom electrode. Two pieces of triboelectric parts were connected via conductive tape for further measurements.

Supplementary Figure 2 | Finite element simulation results. The computed voltage difference between two triboelectric layers of TI film and Kapton via finite element simulation. Note that the simulated spacing between two triboelectric layers was set as 10, 20, and 30 mm, respectively.

Supplementary Figure 3 | Results of the Raman characterization. Raman spectra of the (a) solution-based Bi₂Te₃ film and (b) MBE-based Bi₂Te₃ film, which indicates its high crystallinity of MBE-grown method. Source data are provided as a Source Data file.

Supplementary Figure 4 | Electric performance of the TI-TENGs with different synthetic methods. Output electrical properties of the MBE-based TI-TENG, including (a) transferred charges and (b) current signal. Note that the film thickness and area of the MBE-grown Bi_2Te_3 are 5 nm and 0.5 cm², which are identical with that of the solution-based TI-TENG for a fair comparison. Source data are provided as a Source Data file.

Supplementary Figure 5 | The Controlled experiment of the sapphire-Kapton-based TENG. (a) The measured voltage signal, (b) transferred charges, and (c) measured current signal of the sapphire-Kapton-based TENG, indicating the negligible contributions from the sapphire substrate to the performance of the MBE-based TI-TENG. Source data are provided as a Source Data file.

Supplementary Figure 6 | Images of various triboelectric counterparts. Images of the fabricated triboelectric counterparts with various triboelectric media in the current triboelectric series, including (a) nylon, (b) paper, (c) aluminum (Al), (d) polymethyl methacrylate (PMMA), (e) copper (Cu), (f) Kapton, (g) polydimethylsiloxane (PDMS), (h) fluorinated ethylene propylene (FEP), and (i) polyvinyl chloride (PVC), respectively. Scale bar: 1 cm.

Supplementary Figure 7 The investigation of the Bi₂Se₃ and Bi₂Se₃-NP TI-TENG. (a) SEM image of the hexagonal Bi₂Se₃ nanoplates (Bi₂Se₃ NPs). (b) Surface potential variation of Kapton film (i) before and (ii) after contact with $Bi₂Se₃-NP$ film. (c) and (d) show the measured output voltage and transferred charges of the Bi2Se3-NP TI-TENG with Kapton as the counter triboelectric layer. Source data are provided as a Source Data file.

Supplementary Figure 8 | The collection of the Kapton-based TENGs. It indicates that Kapton is a frequently-used triboelectric material¹⁻⁹.

Supplementary Figure 9 | Performance comparison of the TENGs with/without TI films. Comparison plots of the electrical performance (output voltage (a), transferred charges (b), and output current (c)) between different TENGs with and without TI film, which highlight the dominant role of TI films. Source data are provided as a Source Data file.

Supplementary Figure 10 | Fitting result of the output voltage versus contact area. The output voltage of the Bi_2Te_3-NP TENG varies depending on the contact area from 1 to 25 cm². The fitting line (solid red line) indicates the linear relationship between the voltage signal and the device area. Source data are provided as a Source Data file.

Supplementary Figure 11 | The morphology comparison of the Kapton triboelectric layer after prolonged operation. SEM images of the Kapton film (a) before and (b) after 20000 cycles. The arrows in (b) indicate the few impurities such as $Bi₂Te₃ NP$ on the surface of Kapton after prolonged operation, which lead to negligible impacts on the electrical performance of the TI-TENGs.

Supplementary Figure 12 | Image of the designed TI-TENG sensor array with different spacings. Image of the bottom side of the designed TI-TENG sensor array, which includes 9 ITO electrodes $(1 \times 1 \text{ cm}^2)$ with different spacings (d) ranging from 0 to 7 mm. Scale bar: 1 cm.

Supplementary Figure 13 | Images of the TI-TENG sensor array with identical spacing. (a) Images of 9 ITO electrodes on the bottom side of the designed TI-TENG sensor array with identical spacing (3 mm). (b) Monitored objects on the TI-TENG sensors with the shapes of letters "T" and "I". Scale bar: 1 cm.

Supplementary References

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